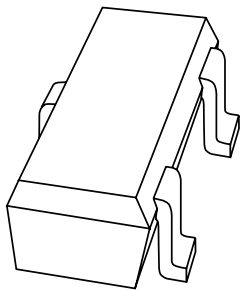


# DATA SHEET



**2PB709AW**

**PNP general purpose transistor**

Product specification

2002 Jun 26

# PNP general purpose transistor

# 2PB709AW

### FEATURES

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

PNP transistor in an SC-70 (SOT323) plastic package.  
NPN complement: 2PD601AW

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
2PB709AQW	N5*
2PB709ARW	N7*
2PB709ASW	N9*

### Note

- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

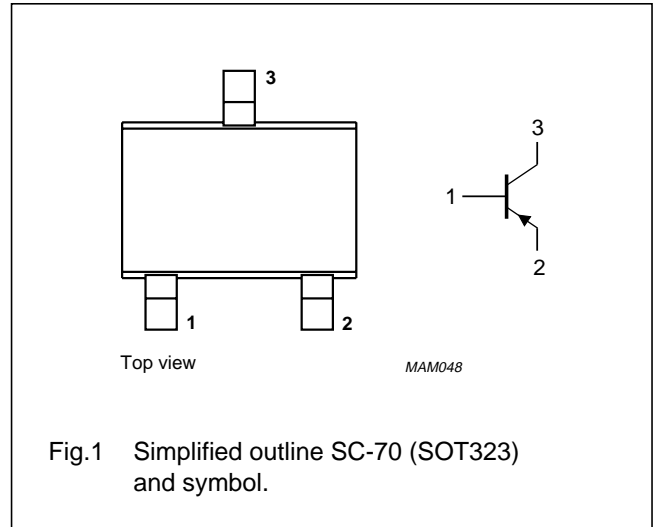


Fig.1 Simplified outline SC-70 (SOT323) and symbol.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–45	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–6	V
I <sub>C</sub>	collector current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	200	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Note

1. For mounting conditions, see “Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18”.

## PNP general purpose transistor

2PB709AW

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

## Note

- For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$I_E = 0; V_{CB} = -45\text{ V}$	–	–10	nA
		$I_E = 0; V_{CB} = -45\text{ V}; T_j = 150\text{ °C}$	–	–5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–10	nA
$h_{FE}$	DC current gain 2PB709AQW 2PB709ARW 2PB709ASW	$I_C = -2\text{ mA}; V_{CE} = -10\text{ V}$	160	260	
			210	340	
			290	460	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -10\text{ mA};$ note 1	–	–500	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V};$ $f = 1\text{ MHz}$	–	5	pF
$f_T$	transition frequency 2PB709AQW 2PB709ARW 2PB709ASW	$I_C = -1\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	60	–	MHz
			70	–	MHz
			80	–	MHz

## Note

- Pulse test:  $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02$ .

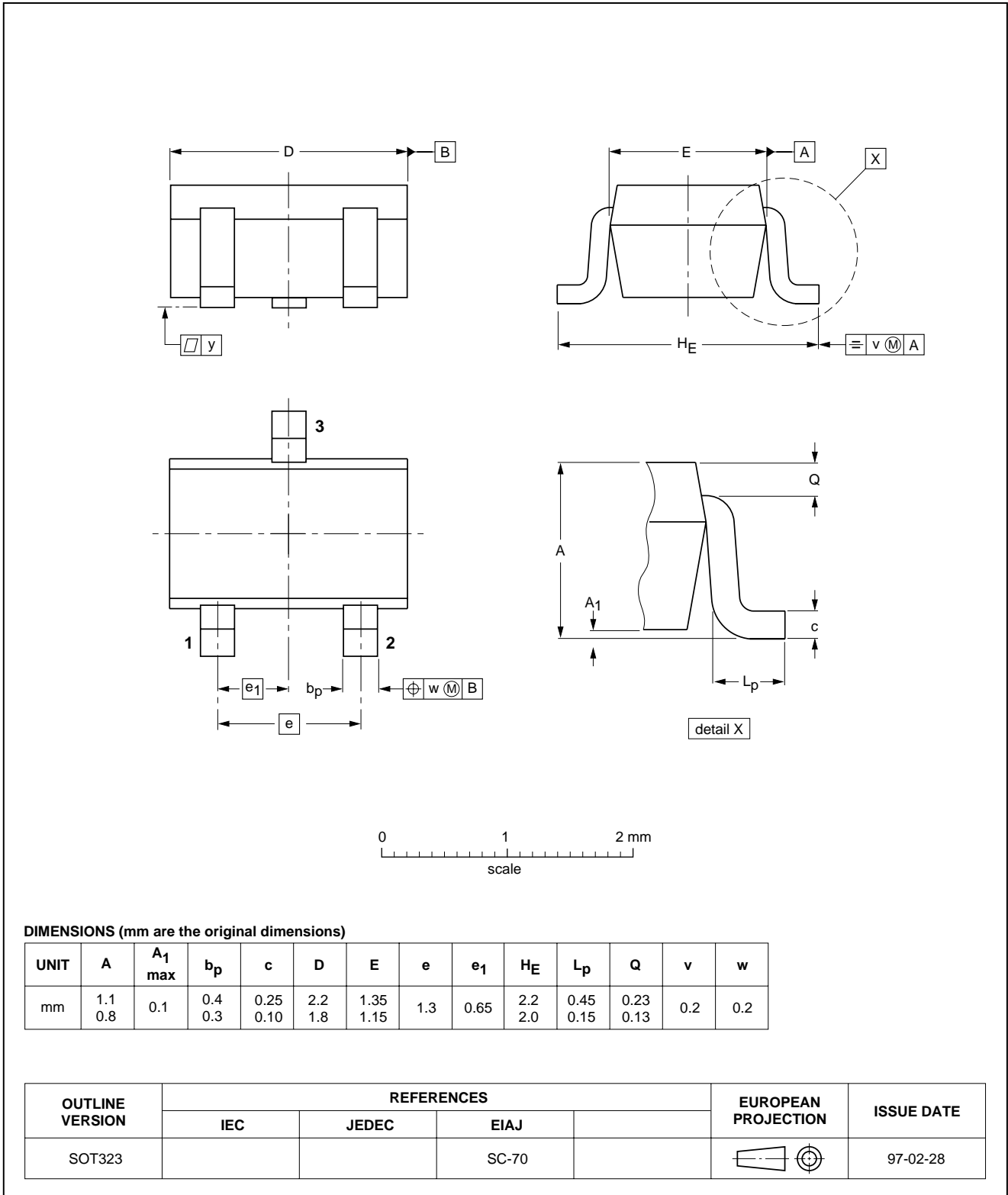
PNP general purpose transistor

2PB709AW

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



## PNP general purpose transistor

2PB709AW

## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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2PB709AW

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**NOTES**

PNP general purpose transistor

2PB709AW

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**NOTES**

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